

Title (en)
Method of fabricating a CIGSS solar cell

Title (de)
Verfahren zur Herstellung einer CIGSS-Solarzelle

Title (fr)
Procédé de fabrication de cellule solaire CIGSS

Publication
EP 2202804 A3 20140528 (EN)

Application
EP 09015528 A 20091216

Priority
KR 20080132465 A 20081223

Abstract (en)
[origin: EP2202804A2] A method of fabricating solar cell is provided according to one or more embodiments. According to an embodiment, the method of fabricating solar cell includes forming a back electrode layer formed on a substrate, forming a light absorbing layer on the back electrode layer, and forming a transparent electrode layer on the light absorbing layer, wherein the light absorbing layer is comprised of copper (Cu), gallium (Ga), indium (In), sulfur (S), and selenium (Se) and includes a first concentration region in which concentrations of sulfur (S) gradually decrease in the light absorbing layer going in a first direction going from the back electrode layer toward a transparent electrode layer, and wherein the forming of the light absorbing layer comprises forming a first precursor comprised of copper (Cu), gallium (Ga) and indium (In) on the back electrode layer, forming a first compound layer by performing a first heat treatment to the first precursor using a sulfur (S) containing gas, forming a second precursor comprised of copper (Cu), gallium (Ga) and indium (In) on the first compound layer, and forming the light absorbing layer by performing a second heat treatment to the first compound layer and the second precursor using a selenium (Se) containing gas.

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Citation (search report)

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